# RENESAS HD74LV1GW07A

Dual Buffer Open Drain

REJ03D0076-0300 Rev.3.00 Sep 08, 2006

### Description

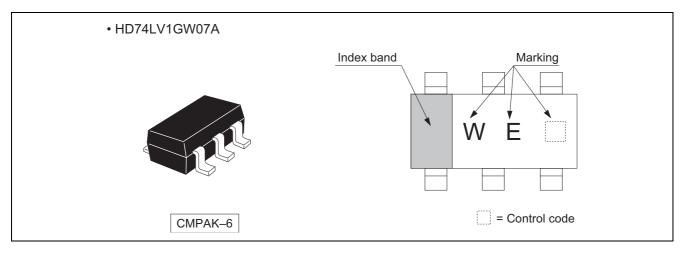
The HD74LV1GW07A has dual buffer open drain in a 6 pin package. Low voltage and high-speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

### Features

- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- Supply voltage range : 1.65 to 5.5 V Operating temperature range : -40 to +85°C
- All inputs  $V_{IH}$  (Max.) = 5.5 V (@V<sub>CC</sub> = 0 V to 5.5 V) All outputs  $V_0$  (Max.) = 5.5 V (@V<sub>CC</sub> = 0 V, Output: Z)
- Output current 6 mA (@ $V_{CC}$  = 3.0 V to 3.6 V), 12 mA (@ $V_{CC}$  = 4.5 V to 5.5 V)
- All the logical input has hysteresis voltage for the slow transition.
- Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74LV1GW07ACME	CMPAK-6 pin	PTSP0006JA-A (CMPAK-6V)	СМ	E (3,000 pcs / Reel)

### **Outline and Article Indication**



### **Function Table**

Input A	Output Y
Н	Z
L	L

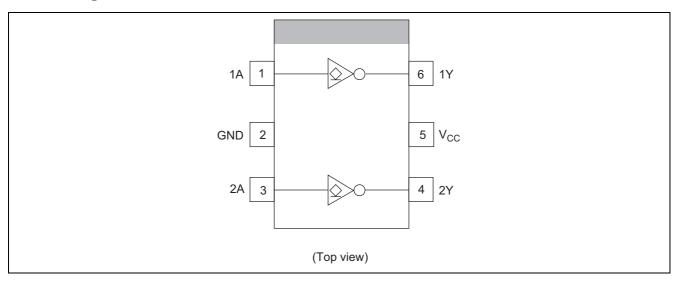
H : High level

L : Low level

Z : High impedance



### **Pin Arrangement**



### **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V <sub>CC</sub>	-0.5 to 7.0	V	
Input voltage range *1	VI	-0.5 to 7.0	V	
Output voltage range *1, 2	M	-0.5 to V <sub>CC</sub> + 0.5	V	Output : L
Output voltage range	Vo	-0.5 to 7.0	v	V <sub>CC</sub> : OFF or Output : Z
Input clamp current	l <sub>IK</sub>	-20	mA	V <sub>1</sub> < 0
Output clamp current	I <sub>ОК</sub>	-50	mA	V <sub>0</sub> < 0
Continuous output current	lo	±25	mA	$V_0 = 0$ to $V_{CC}$
Continuous current through V <sub>CC</sub> or GND	I <sub>CC</sub> or I <sub>GND</sub>	±50	mA	
Maximum power dissipation at Ta = $25^{\circ}$ C (in still air) <sup>*3</sup>	PT	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. This value is limited to 5.5 V maximum.

3. The maximum package power dissipation was calculated using a junction temperature of 150°C.



### **Recommended Operating Conditions**

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V <sub>CC</sub>	1.65	5.5	V	
Input voltage range	VI	0	5.5	V	
Output voltage range	Vo	0	V <sub>cc</sub>	V	
		—	1		V <sub>CC</sub> = 1.65 to 1.95 V
Output current	I <sub>OL</sub>	—	2	mA	$V_{CC}$ = 2.3 to 2.7 V
		—	6	IIIA	$V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$
		—	12		$V_{CC} = 4.5 \text{ to } 5.5 \text{ V}$
		0	300		V <sub>CC</sub> = 1.65 to 1.95 V
Input transition rise or fall rate	$\Delta t / \Delta v$	0	200	ns / V	$V_{CC}$ = 2.3 to 2.7 V
	$\Delta t / \Delta v$	0	100	115 / V	$V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$
		0	20		$V_{CC}$ = 4.5 to 5.5 V
Operating free-air temperature	Ta	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

### **Electrical Characteristic**

							$Ta = -40 \text{ to } 85^{\circ}\text{C}$
ltem	Symbol	V <sub>cc</sub> (V) * <sup>1</sup>	Min	Тур	Max	Unit	Test Condition
		1.65 to 1.95	$V_{CC} \times 0.75$	—	—		
	V	2.3 to 2.7	V <sub>CC</sub> ×0.7	—	—		
	V <sub>IH</sub>	3.0 to 3.6	V <sub>CC</sub> ×0.7	—	—		
Input voltage		4.5 to 5.5	V <sub>CC</sub> ×0.7	—	—	V	
input voltage		1.65 to 1.95	—	—	V <sub>CC</sub> ×0.25	v	
	V	2.3 to 2.7	—	_	V <sub>CC</sub> ×0.3		
	VIL	3.0 to 3.6	—	_	V <sub>CC</sub> ×0.3		
		4.5 to 5.5	—	_	V <sub>CC</sub> ×0.3		
		1.8	—	0.25	—	V	
Hysteresis voltage	V <sub>H</sub>	2.5	—	0.30	—		$V_{T}^{+} - V_{T}^{-}$
Hysteresis voltage	∨н	3.3	—	0.35	—		$v_{T} = v_{T}$
		5.0	—	0.45	—		
		Min to Max	—	_	0.1		I <sub>OL</sub> = 50 μA
		1.65	—	_	0.3	V	I <sub>OL</sub> = 1 mA
Output voltage	V <sub>OL</sub>	2.3	—	_	0.4		$I_{OL} = 2 \text{ mA}$
		3.0	—	_	0.44		$I_{OL} = 6 \text{ mA}$
		4.5	—	_	0.55		I <sub>OL</sub> = 12 mA
Input current	I <sub>IN</sub>	0 to 5.5	—	_	±1	μA	$V_{IN} = 5.5 \text{ V or GND}$
Off state	I <sub>oz</sub>	Min to Max	_	_	±5	μA	$V_{0} = 5.5 \text{ V or GND}$
output current	102				_0	μι	-
Quiescent supply current	I <sub>CC</sub>	5.5	_	_	10	μA	$V_{IN} = V_{CC}$ or GND, $I_O = 0$
Output leakage current	I <sub>OFF</sub>	0	_	_	5	μΑ	$V_{\rm IN}$ or $V_{\rm O}$ = 0 to 5.5 V
Input capacitance	CIN	3.3	—	3.0		pF	$V_{IN} = V_{CC}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

Ta = -40 to  $85^{\circ}C$ 



## **Switching Characteristics**

 $V_{CC} = 1.8 \pm 0.15 \text{ V}$ 

Item	Symbol	-	Га = 25°С	;	Ta = -40 to 85°C		Unit	Test	FROM	то
nem	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation	t <sub>ZL</sub>	_	12.6	22.0	1.0	24.0	20	C <sub>L</sub> = 15 pF	٨	V
delay time	t <sub>LZ</sub>		19.7	33.0	1.0	36.0	ns	C <sub>L</sub> = 50 pF	A	T

 $V_{CC}=2.5\pm0.2~V$ 

Item	Symbol		Га = 25°С	;	Ta = -40	to 85°C	Unit	Test	FROM	то
nem	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation	t <sub>ZL</sub>	_	7.0	11.7	1.0	14.0	20	C <sub>L</sub> = 15 pF	۸	V
delay time	t <sub>LZ</sub>		10.5	15.5	1.0	18.0	ns	C <sub>L</sub> = 50 pF	A	I

 $V_{CC}=3.3\pm0.3~V$ 

Item	Symbol	٦	Га = 25°С	;	Ta = -40	to 85°C	Unit	Test	FROM	то
nem	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Propagation	t <sub>ZL</sub>	Ι	5.0	7.1	1.0	8.5	20	C <sub>L</sub> = 15 pF	٨	V
delay time	t <sub>LZ</sub>	_	7.5	10.6	1.0	12.0	ns	C <sub>L</sub> = 50 pF	A	I

 $V_{CC}=5.0\pm0.5~V$ 

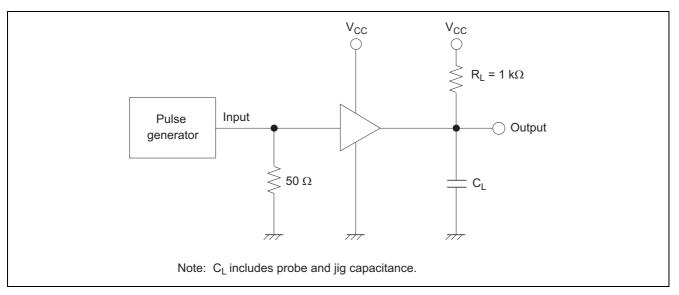
Item	Symbol	-	Га = 25°С	;	Ta = -40	to 85°C	Unit	Test	FROM	то
item	Symbol	Min	Тур	Max	Min	Max	Onic	Conditions	(Input)	(Output)
Propagation	t <sub>ZL</sub>		3.8	5.5	1.0	6.5	ns	C <sub>L</sub> = 15 pF	٨	v
delay time	t <sub>LZ</sub>	_	5.3	7.5	1.0	8.5	115	$C_L = 50 \text{ pF}$	A	I

## **Operating Characteristics**

 $C_L = 50 \text{ pF}$ 

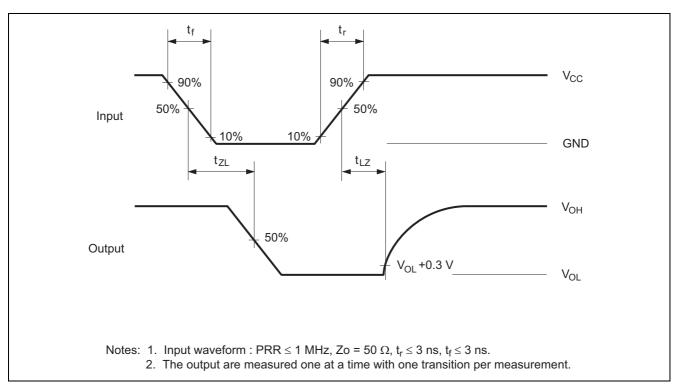
ltem	Symbol	V., 00	٦	Га = 25°С	;	Unit	Test Conditions	
nem	Symbol	V <sub>cc</sub> (V)	Min	Тур	Max	Unit	Test Conditions	
Power dissipation	<b>C</b>	3.3	_	8.5		ρF	f = 10 MHz	
capacitance	CPD	5.0	—	10.0		рг		

## **Test Circuit**

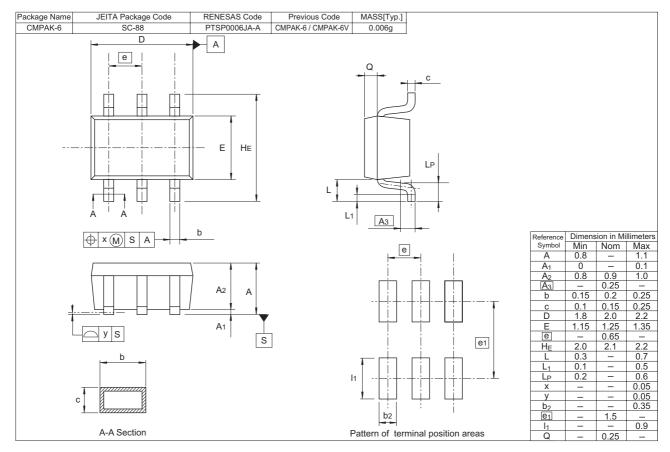




### Waveform



### **Package Dimensions**





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